

#### ABSTRACT OF THE DISCLOSURE

A method for fabricating a III-V Group compound semiconductor comprising a step of epitaxially growing on an  $Al_xGa_{1-x}As$  layer of lower Al content an  $Al_xGa_{1-x}As$  layer of 5 higher Al content, in which step a growth rate of the  $Al_xGa_{1-x}As$  layer of higher Al content is made slower than a growth rate of the  $Al_xGa_{1-x}As$  layer of lower Al content, thereby effectively inhibiting the occurrence of starting points of abnormal growth at the interface between the two layers.